TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

## T C 7 M A 1 5 7 F K

Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

The TC7MA157FK is a high performance CMOS multiplexer. Designed for use in 1.8, 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

It consists of four 2-input digital multiplexers with common select and strobe inputs.

When the ST input is held "H" level, selection of data is inhibited and all the outputs become "L" level. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.

All inputs are equipped with protection circuits against static discharge.

#### Features

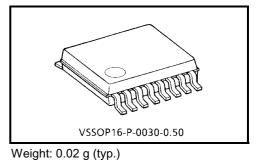
- Low voltage operation:  $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation:  $t_{pd} = 3.0 \text{ ns} (\text{max}) (\text{V}_{CC} = 3.0 \sim 3.6 \text{ V})$  $t_{pd} = 3.5 \text{ ns} (\text{max}) (\text{V}_{CC} = 2.3 \sim 2.7 \text{ V})$

$$pd = 7.0 ns (max) (VCC = 1.8 V)$$

- Output current:  $IOH/IOL = \pm 24 \text{ mA} (min) (VCC = 3.0 \text{ V})$  $IOH/IOL = \pm 18 \text{ mA} (min) (VCC = 2.3 \text{ V})$  $IOH/IOL = \pm 6 \text{ mA} (min) (VCC = 1.8 \text{ V})$
- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model >  $\pm 2000$  V

- Package: VSSOP (US16)
- Power down protection is provided on all inputs and outputs.



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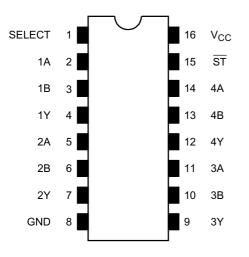
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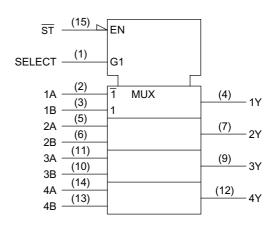
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## **TOSHIBA**

#### Pin Assignment (top view)



#### **IEC Logic Symbol**



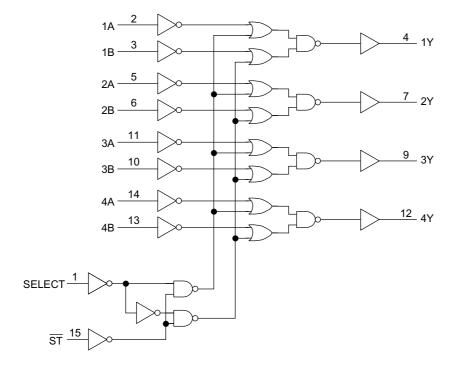
#### **Truth Table**

	Inputs						
ST	SELECT	А	В	Y			
Н	х	Х	Х	L			
L	L	L	Х	L			
L	L	Н	Х	Н			
L	Н	Х	L	L			
L	Н	Х	Н	Н			

X: Don't care

### **TOSHIBA**

#### System Diagram



#### **Maximum Ratings**

Characteristics	Characteristics Symbol Rating		Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~4.6	V	
DC input voltage	V <sub>IN</sub>	-0.5~4.6	V	
DC output voltage	Vout	-0.5~4.6 (Note1)	V	
De ouput voltage	VOUT	-0.5~V <sub>CC</sub> + 0.5 (Note2)	v	
Input diode current	I <sub>IK</sub>	-50	mA	
Output diode current	I <sub>OK</sub>	±50 (Note3)	mA	
DC output current	IOUT	±50	mA	
Power dissipation	PD	180	mW	
DC V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note1:  $V_{CC} = 0 V$ 

Note2: High or low state.  $\ensuremath{\mathsf{I}}_{\ensuremath{\mathsf{OUT}}}$  absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

#### **Recommended Operating Range**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	1.8~3.6	V
Supply Voltage	v CC	1.2~3.6 (Note4	
Input voltage	V <sub>IN</sub>	-0.3~3.6	V
Output voltage	Vout	0~3.6 (Note5	) V
Output voltage	VOUT	0~V <sub>CC</sub> (Note6	
		±24 (Note7	)
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±18 (Note8	) mA
		±6 (Note9	)
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10	) ns/V

Note4: Data retention only

Note5:  $V_{CC} = 0 V$ 

Note6: High or low state

Note7:  $V_{CC} = 3.0 \sim 3.6 \text{ V}$ 

Note8:  $V_{CC} = 2.3 \sim 2.7 \text{ V}$ 

Note9:  $V_{CC} = 1.8 V$ 

Note10:  $V_{IN} = 0.8 \sim 2.0 \text{ V}, \text{ V}_{CC} = 3.0 \text{ V}$ 

#### **Electrical Characteristics**

#### DC Characteristics (Ta = -40~85°C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Characte	ristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Input voltage	High level	VIH		_	2.7~3.6	2.0		V
input voltage	Low level	VIL			2.7~3.6	_	0.8	v
				I <sub>OH</sub> = -100 μA	2.7~3.6	V <sub>CC</sub> - 0.2	_	
	High level	V <sub>OH</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_	
	-			I <sub>OH</sub> = -18 mA	3.0	2.4	_	
Output voltage			I <sub>OH</sub> = -24 mA	3.0	2.2		V	
			$I_{OL} = 100 \ \mu A$	2.7~3.6	_	0.2		
	Low level	Vei	$V_{OL}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 12 \text{ mA}$	2.7	_	0.4	
	Low level	VOL		I <sub>OL</sub> = 18 mA	3.0	_	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	_	0.55	
Input leakage curr	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.7~3.6	_	±5.0	μA
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μA
Quiescent supply current			$V_{IN} = V_{CC}$ or GND		2.7~3.6	_	20.0	
		ICC	$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		2.7~3.6	_	±20.0	μA
Increase in I <sub>CC</sub> pe	er input	Δl <sub>CC</sub>	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6		750	

#### DC Characteristics (Ta = -40~85°C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit
Characteri	Characteristics Sy				$V_{CC}(V)$	IVIIII	IVIAX	Onit
Input voltage	High level	VIH		—	2.3~2.7	1.6	_	v
Input voltage	Low level	VIL		_	2.3~2.7		0.7	v
			I <sub>OH</sub> = -100 μA	2.3~2.7	V <sub>CC</sub> - 0.2	_		
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -6 mA	2.3	2.0	_	
			I <sub>OH</sub> = -12 mA	2.3	1.8	_		
Output voltage				I <sub>OH</sub> = -18 mA	2.3	1.7	_	V
				I <sub>OL</sub> = 100 μA	2.3~2.7	_	0.2	
	Low level	V <sub>OL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 12 mA	2.3	_	0.4	
				I <sub>OL</sub> = 18 mA	2.3		0.6	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.3~2.7		±5.0	μA
Power off leakage current $I_{OFF}$ $V_{IN}$ , V		V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μA	
Ouissant sugal, sugart	Icc	$V_{IN} = V_{CC}$ or GND		2.3~2.7		20.0		
Quiescent supply c	Quiescent supply current		$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		2.3~2.7		±20.0	μA

#### DC Characteristics (Ta = -40~85°C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Characteris	stics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Input voltage	High level	VIH			1.8~2.3	$0.7 \times V_{CC}$		V
input voltage	Low level	V <sub>IL</sub>			1.8~2.3		$0.2 \times V_{CC}$	v
	High level	Voh	VIN = VIH or VIL	I <sub>OH</sub> = -100 μA	1.8	V <sub>CC</sub> - 0.2	_	
Output voltage		_		I <sub>OH</sub> = -6 mA	1.8	1.4	_	V
	Low level	Vol	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>II</sub>	$I_{OL} = 100 \ \mu A$	1.8	—	0.2	
Low level		VOL	VIN = VIH OL VIL	$I_{OL} = 6 \text{ mA}$	1.8	_	0.3	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		1.8	_	±5.0	μA
Power off leakage c	urrent	IOFF	$V_{IN}$ , $V_{OUT} = 0 \sim 3.6 V$		0	_	10.0	μA
Quiescent supply current		loo	$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	μA
		ICC	$V_{CC} \leq V_{IN} \leq 3.6 \text{ V}$		1.8		±20.0	μА

#### AC Characteristics (Ta = -40~85°C, Input: t<sub>r</sub> = t<sub>f</sub> = 2.0 ns, C<sub>L</sub> = 30 pF, R<sub>L</sub> = 500 $\Omega$ )

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Max	Unit
			1.8	1.0	7.0	
Propagation delay time (A, B-Y)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5\pm0.2$	0.8	3.5	ns
(A, D-1)	t <sub>pHL</sub>		$3.3\pm0.3$	0.6	3.0	
Propagation delay time (SELECT-Y)	4	Figure 1, Figure 2	1.8	1.0	9.0	
	t <sub>pLH</sub> t <sub>pHL</sub>		$2.5\pm0.2$	0.8	4.5	ns
			$3.3\pm0.3$	0.6	3.5	
Drengestion delay time	4		1.8	1.0	9.0	
Propagation delay time ( ST -Y)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5\pm0.2$	0.8	4.5	ns
(31-1)	t <sub>pHL</sub>		$3.3\pm0.3$	0.6	3.5	
Output to output skew		(Note11)	1.8	_	0.5	
	t <sub>osLH</sub>		$2.5\pm0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3\pm 0.3$	—	0.5	

For  $C_L = 50 \text{ pF}$ , add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.  $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$ 

#### Dynamic Switching Characteristics (Ta = $25^{\circ}$ C, Input: t<sub>r</sub> = t<sub>f</sub> = 2.0 ns, C<sub>L</sub> = 30 pF)

Characteristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Тур.	Unit
		$V_{IH} = 1.8 V, V_{IL} = 0 V$ (N	lote12)	1.8	0.25	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$V_{IH} = 2.5 V, V_{IL} = 0 V$ (N	lote12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote12)	3.3	0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote12)	1.8	-0.25	
Quiet output minimum dynamic $V_{OL}$	V <sub>OLV</sub>	$V_{IH} = 2.5 V, V_{IL} = 0 V$ (N	lote12)	2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote12)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote12)	1.8	1.5	
Quiet output minimum dynamic $V_{OH}$	VOHV	$V_{IH} = 2.5 V, V_{IL} = 0 V$ (N	lote12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

#### **Capacitive Characteristics (Ta = 25°C)**

Characteristics	Symbol	Symbol Test Condition			Тур.	Unit
Characteristics	Cymbol		$V_{CC}(V)$	тур.	Unit	
Input capacitance	C <sub>IN</sub>	—		1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C <sub>PD</sub>	$f_{IN} = 10 \text{ MHz}$	(Note13)	1.8, 2.5, 3.3	20	pF

Note13: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

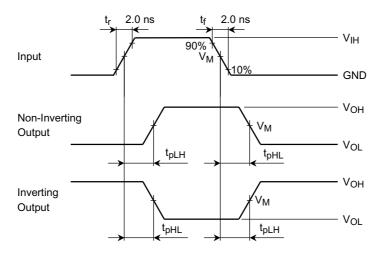
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

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#### **AC Waveform**



Symbol	V <sub>CC</sub>						
Symbol	$3.3\pm0.3\;V$	$2.5\pm0.2\;V$	1.8 V				
VIH	2.7 V	V <sub>CC</sub>	V <sub>CC</sub>				
VM	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2				

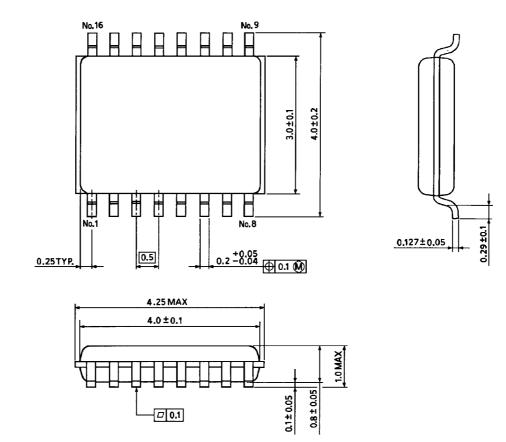
 $R_L = 500 \ \Omega$ 



#### **Package Dimensions**

VSSOP16-P-0030-0.50

Unit : mm



Weight: 0.02 g (typ.)